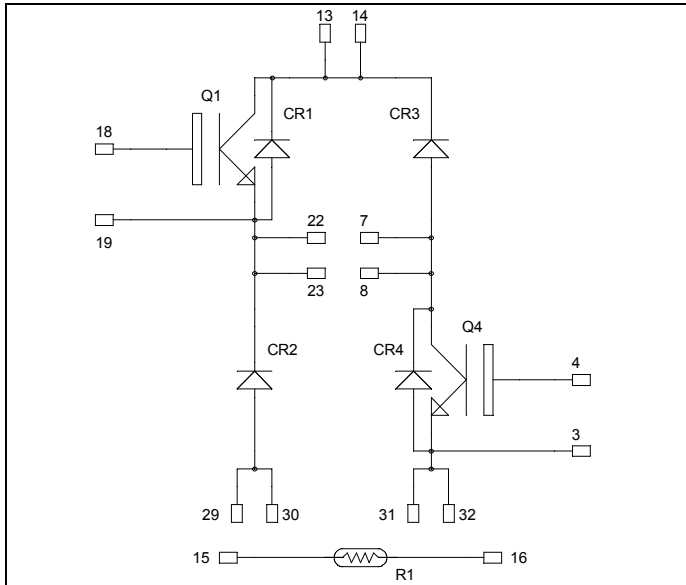


## Asymmetrical - Bridge NPT IGBT Power Module

$V_{CES} = 600V$   
 $I_C = 90A @ T_c = 80^\circ C$

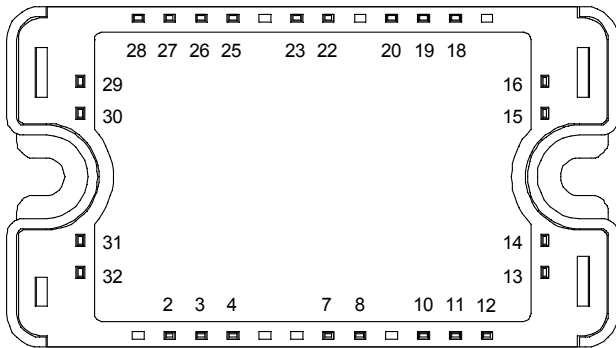


### Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring



### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- RoHS compliant

All multiple inputs and outputs must be shorted together  
 Example: 13/14 ; 29/30 ; 22/23 ...

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	110	A
		$T_c = 80^\circ C$	90	
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	200	
$V_{GE}$	Gate - Emitter Voltage		$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	416	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	200A @ 600V	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 100\text{A}$	$T_j = 25^\circ\text{C}$	2	2.5	V
			$T_j = 125^\circ\text{C}$	2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5\text{mA}$	4.5	5.5	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}; V_{CE} = 25\text{V}$		4.3		nF
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.4		
$Q_G$	Gate charge	$V_{GE} = 15\text{V}; V_{CE} = 300\text{V}$ $I_C = 100\text{A}$		240		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 100\text{A}$ $R_G = 2.2\Omega$		25		ns
$T_r$	Rise Time			10		
$T_{d(off)}$	Turn-off Delay Time			130		
$T_f$	Fall Time			20		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 100\text{A}$ $R_G = 2.2\Omega$		25		ns
$T_r$	Rise Time			11		
$T_{d(off)}$	Turn-off Delay Time			150		
$T_f$	Fall Time			30		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 100\text{A}$ $R_G = 2.2\Omega$	$T_j = 125^\circ\text{C}$	1		mJ
$E_{off}$	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$	3		
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15\text{V}; V_{Bus} = 360\text{V}$ $t_p \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		450		A

## Diode ratings and characteristics (CR2 & CR3)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$I_F$	DC Forward Current		$T_c = 80^\circ\text{C}$	100		A
$V_F$	Diode Forward Voltage	$I_F = 100\text{A}$		1.6	2	V
		$I_F = 200\text{A}$		2		
		$I_F = 100\text{A}$	$T_j = 125^\circ\text{C}$	1.3		
$t_{rr}$	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 400\text{V}$	$T_j = 25^\circ\text{C}$	160		ns
			$T_j = 125^\circ\text{C}$	220		
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	290		nC
			$T_j = 125^\circ\text{C}$	1530		

CR1 & CR4 are IGBT protection diodes only

**Temperature sensor NTC** (see application note APT0406 on [www.microsemi.com](http://www.microsemi.com) for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B	T <sub>C</sub> = 100°C		4		%

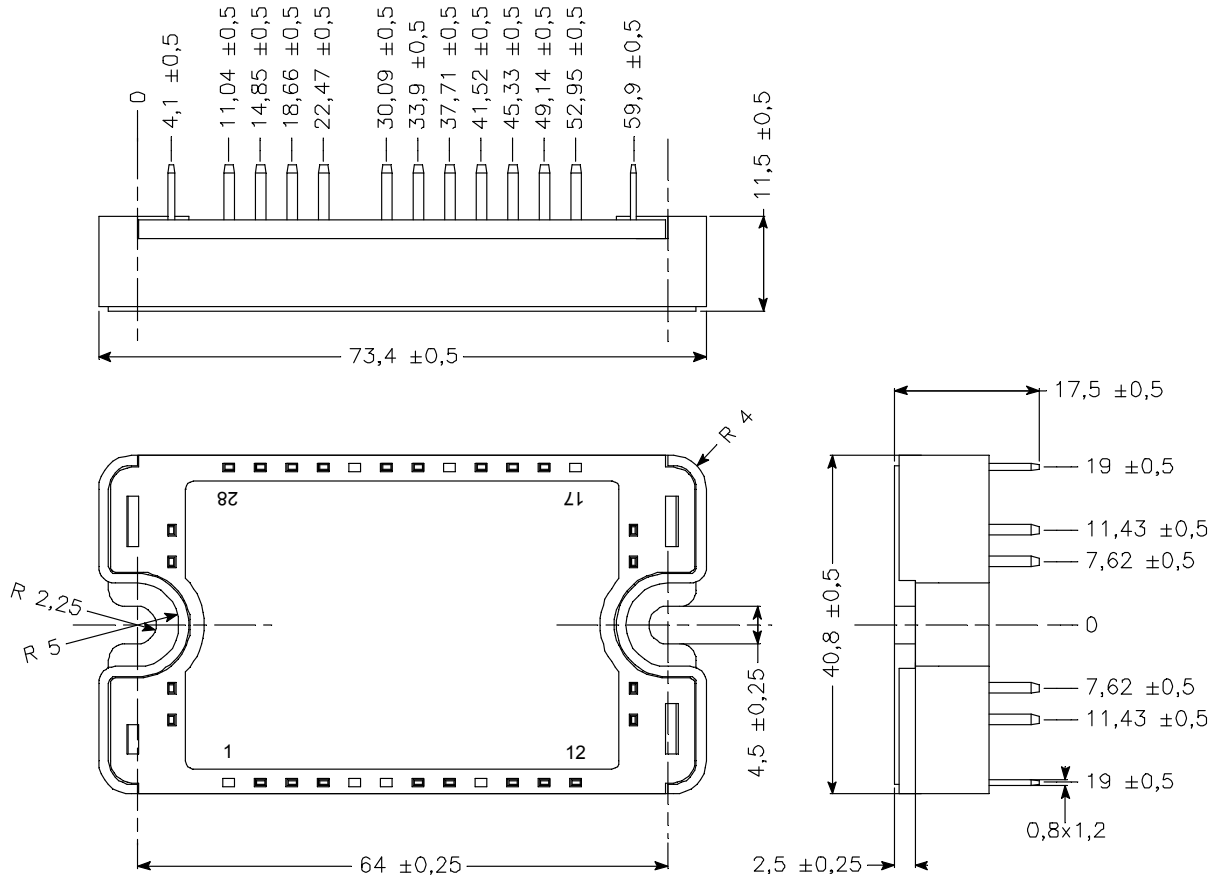
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

## Thermal and package characteristics

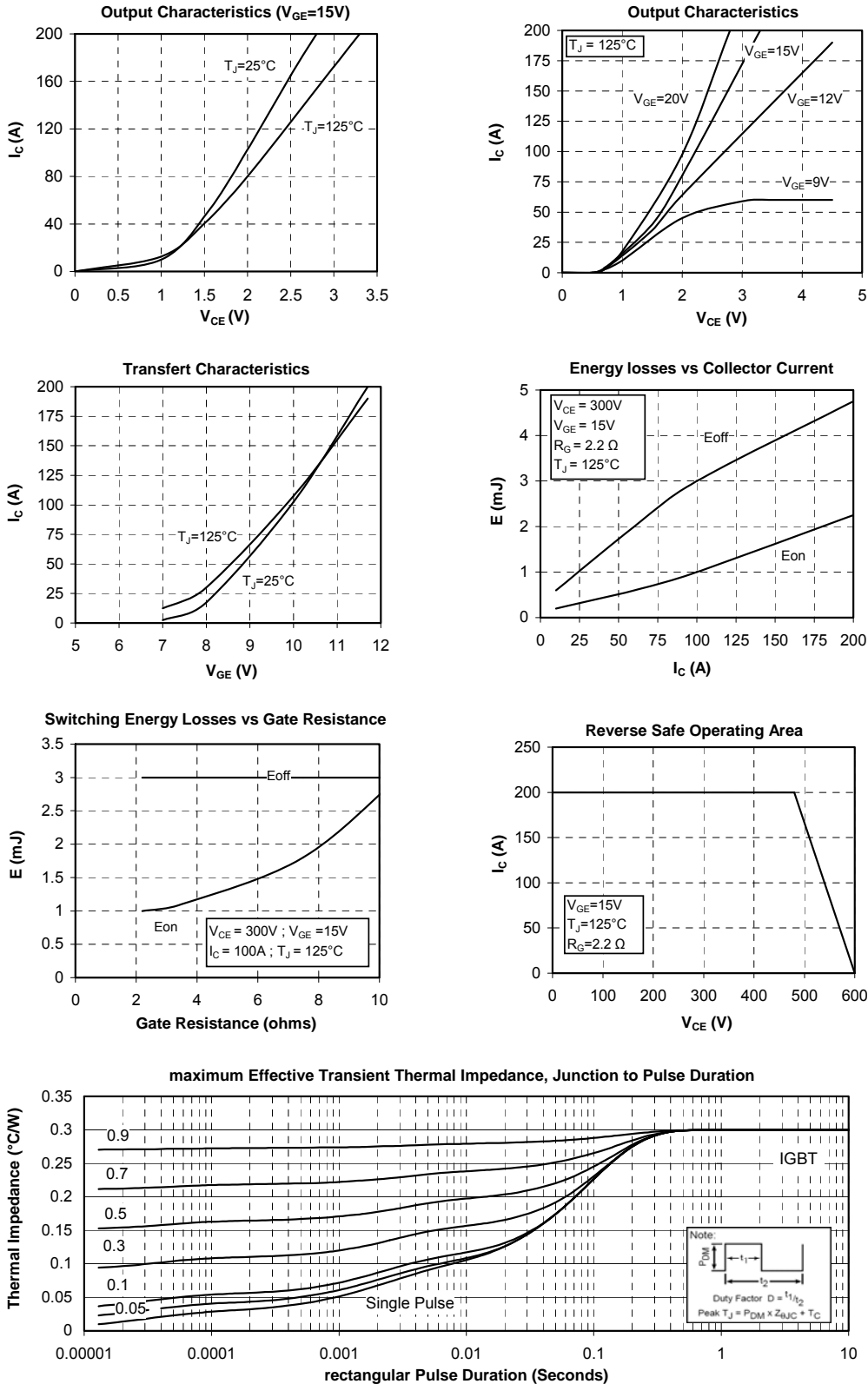
Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.3	°C/W	
		Diode		0.55		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, I <sub>isol</sub> < 1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

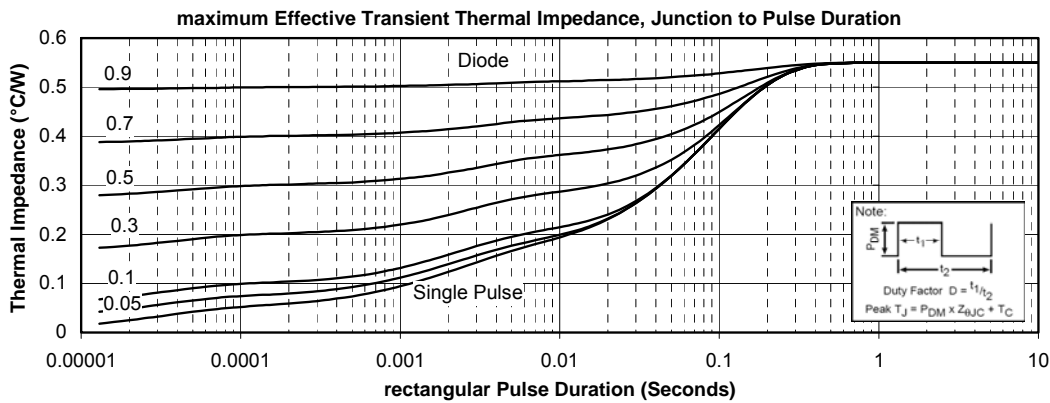
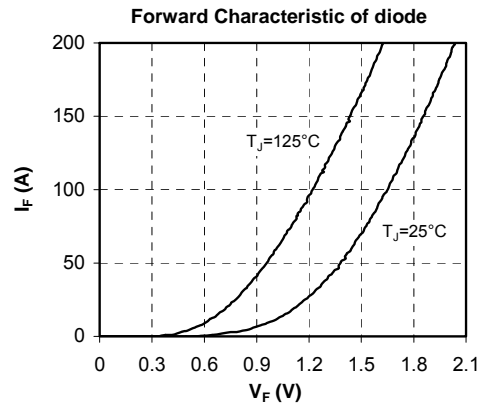
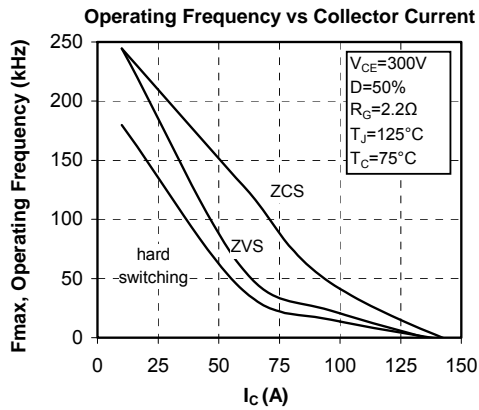
## SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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